

*ABSTRACT AMENDMENT*

Replace the Abstract with:

The cleaning composition for removing resists includes a salt of hydrofluoric acid and a base not containing a metal (A component), a water-soluble organic solvent (B1 component), at least one ~~acid selected from a group consisting of~~ organic acid ~~and or~~ inorganic acid (C component), water (D component), and, optionally, an ammonium salt (E1 component), and ~~its hydrogen ion concentration (pH) is having a pH 4-8.~~ Thus, in ~~the~~ manufacturing ~~process~~ of a semiconductor device, such as a copper interconnecting process, ~~removing efficiency of removing~~ resist residue and other etching residue after etching or ashing ~~improves is improved~~, and corrosion resistance of ~~a~~ copper and ~~an~~ insulating film ~~is also improves improved~~.